

# SILICON MIXER DIODE

## DESCRIPTION:

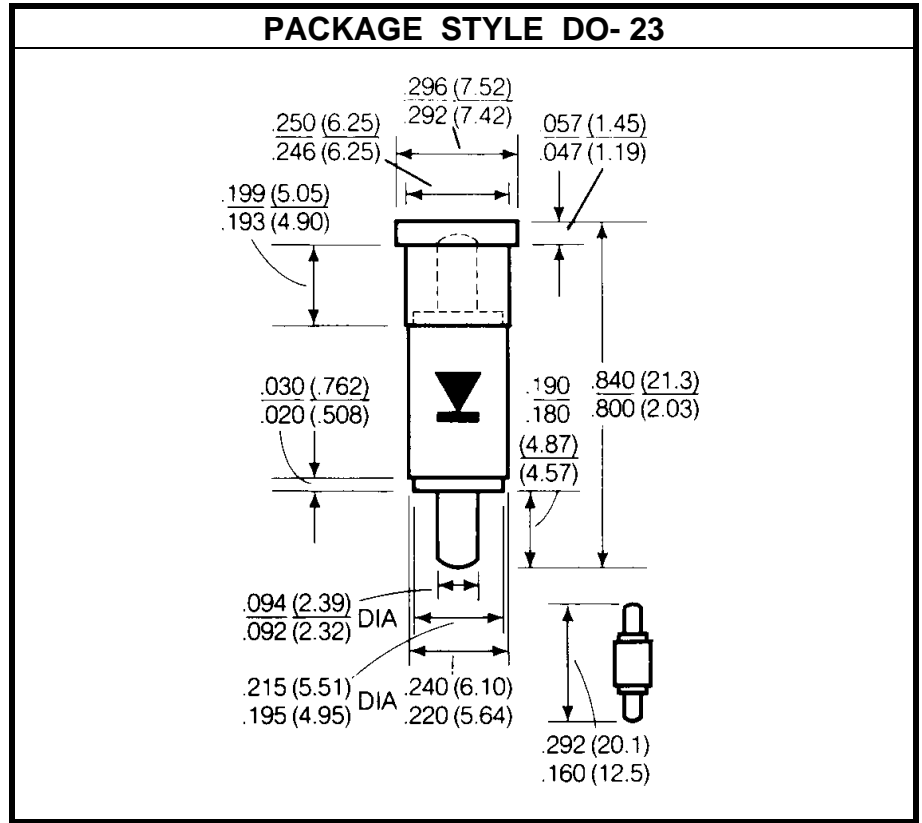
The **ASI 1N21WE** is a Silicon Mixer Diode Designed for Applications Operating From 8.0 to 12.4 GHz.

## FEATURES:

- High burnout resistance
- Low noise figure
- Hermetically sealed package

## MAXIMUM RATINGS

<b>I<sub>F</sub></b>	20 mA
<b>V<sub>R</sub></b>	1.0 V
<b>P<sub>DISS</sub></b>	5.0 (ERGS) @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +150 °C
<b>T<sub>STG</sub></b>	-55 °C to +150 °C



## CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIM	UNITS
<b>N<sub>F</sub></b>	F = 3060 MHz R <sub>L</sub> = 100 Ω	P <sub>lo</sub> = 0.5 mW I <sub>F</sub> = 30 MHz	N <sub>Fif</sub> = 1.5 dB			7.0	dB
<b>V<sub>SWR</sub></b>						1.3	
<b>Z<sub>IF</sub></b>	R <sub>L</sub> = 22 Ω		f = 1000 Hz	350		450	Ω
<b>frange</b>				8.0		12.4	GHz

# Mouser Electronics

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